













ESD

TVS

TSS

MOV

GDT

PLED

AZC199-02S-MS

Product specification



AZC199-02S-MS

Features

- Stand-off voltage: 5V Max
- Transient protection for each line according to
 IEC61000-4-2 (ESD): ±20kV (contact and air discharge)
 IEC61000-4-4 (EFT): 40A (5/50ns)

IEC61000-4-5 (surge): 4A (8/20µs)

- Ultra-low capacitance: CJ = 0.4pF typ.
- Ultra-low leakage current: IR <1nA typ.
- Low clamping voltage: VCL = 20V @ IPP = 16A(TLP)
- Solid-state silicon technology

Reference News

Application

- USB 2.0 and USB 3.0
- HDMI 1.3 and HDMI 1.4
- SATAand eSATA
- DVI
- IEEE 1394
- PCI Express
- Portable Electronics
- Notebooks

PACKAGE OUTLINE	Circuit diagram	Pin Configuration	Marking
SOT-23	GND 3 1 2 1/01 1/02		C11XY



Absolute Maximum Ratings (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Rating	Unit	
Peak pulse power ($t_p = 8/20 \mu s$)	P _{pk}	60	W	
Peak pulse current ($t_p = 8/20 \mu s$)	I _{PP}	4	А	
ESD according to IEC61000-4-2 air discharge				
ESD according to IEC61000-4-2 contact discharge	– V _{ESD}	±20	kV	
Junction temperature	TJ	125	°C	
Operating temperature	T _{OP}	-40~85	°C	
Lead temperature	TL	260	°C	
Storage temperature	T _{STG}	-55~ 150	°C	

Electrical characteristics (TA=25 oC, unless otherwise noted)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Reverse maximum working voltage	V _{RWM}				5.0	V
Reverse leakage current	IR	V _{RWM} = 5V		<1	100	nA
Reverse breakdown voltage	V_{BR}	I _T = 1mA	7.0	8.0	9.0	V
Forward voltage	VF	I _T = 10mA	0.6	0.9	1.2	V
Clamping voltage 1)	V _{CL}	I _{PP} = 16A, t _p = 100ns		20		V
Dynamic resistance 1)	R _{DYN}			0.65		Ω
Clamping voltage ²⁾	V _{CL}	$I_{PP} = 1A, t_p = 8/20 \mu s$			11	V
		$I_{PP} = 4A, t_p = 8/20 \mu s$			15	V
lunction conscitance	CJ	$V_R = 0V$, f = 1MHz Any I/O pin to GND		0.40	0.65	pF
Junction capacitance		V _R = 0V, f = 1MHz Between any I/O pin		0.25	0.40	pF

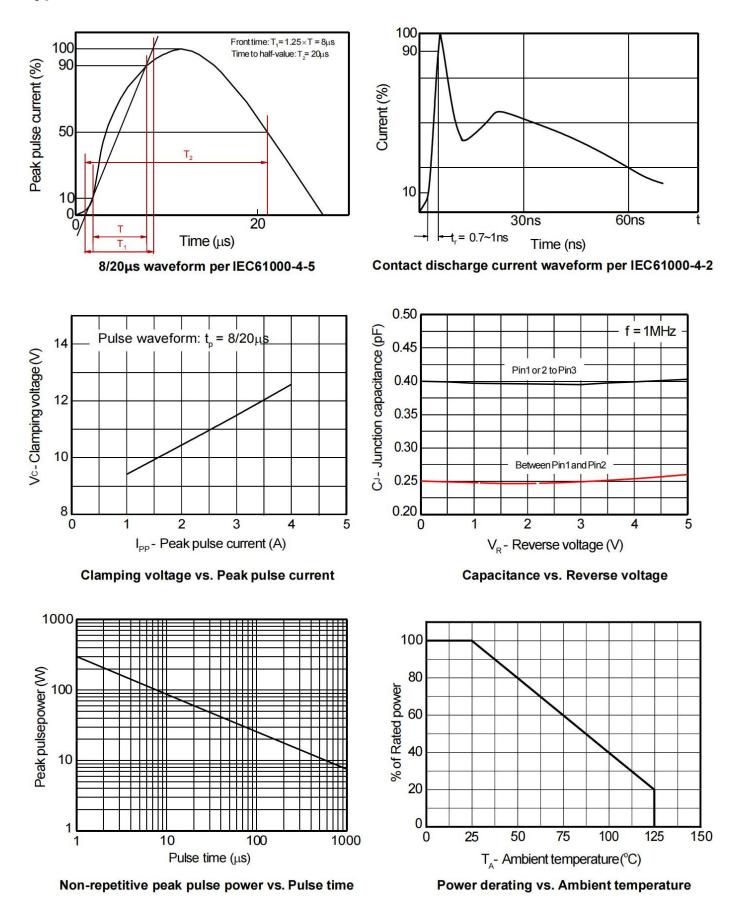
Notes:

1) TLP parameter: Z0 = 50 Ω , tp = 100ns, tr = 2ns, averaging window from 60ns to 80ns. RDYN is calculated from 4A to 16A.

2) According to IEC61000-4-5.

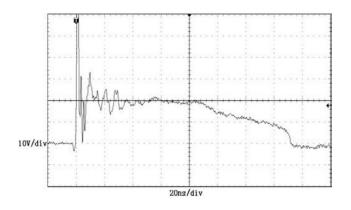


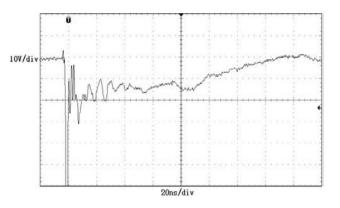
Typical characteristics (TA=25 oC, unless otherwise noted)



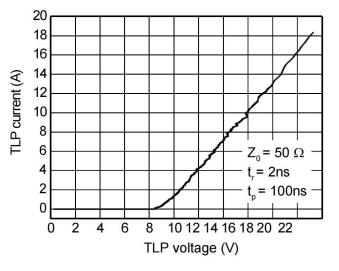


Typical characteristics (TA=25 oC, unless otherwise noted)





ESD clamping (+8kV contact discharge per IEC61000-4-2)

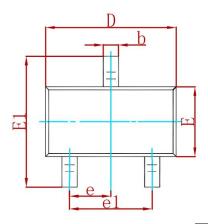


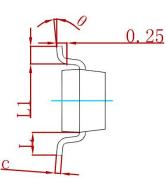
TLP Measurement

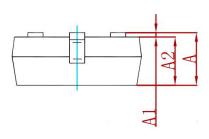
ESD clamping (-8kV contact discharge per IEC61000-4-2)



PACKAGE MECHANICAL DATA

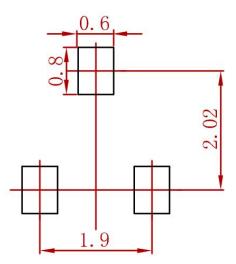






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
A	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022	2 REF	
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

Suggested Pad Layout



Note:

1.Controlling dimension: in millimeters.

2.General tolerance:±0.05mm.

3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
AZC199-02S-MS	SOT-23	3000



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